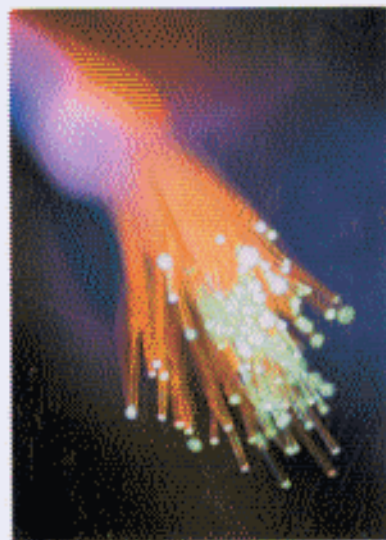
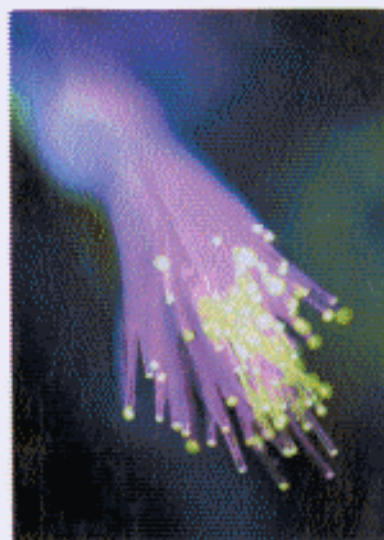
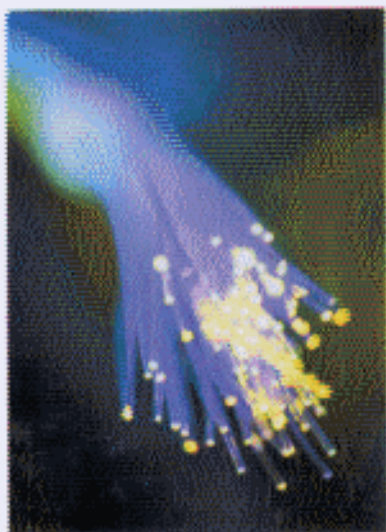
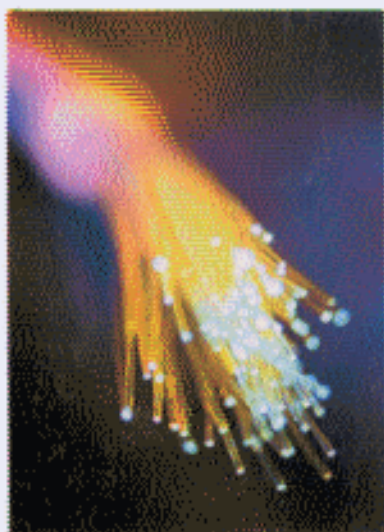


Photodetectors and Fiber Optics

Edited by **Hari Singh Nalwa**



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